



SHANGHAI SUNRISE ELECTRONICS CO., LTD.

## D8SB10 THRU D8SB100

SINGLE PHASE GLASS

PASSIVATED SIP BRIDGE RECTIFIER

**VOLTAGE: 100 TO 1000V CURRENT: 8.0A**

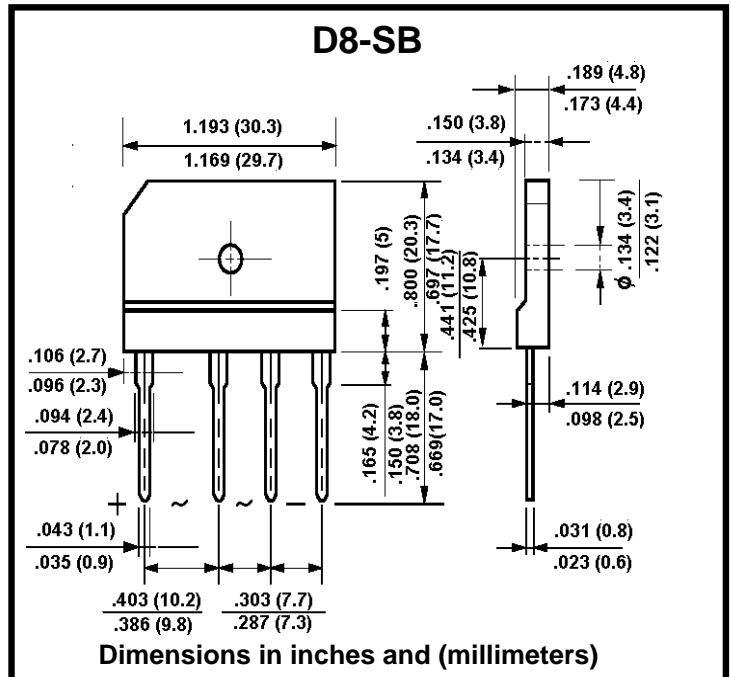
TECHNICAL  
SPECIFICATION

### FEATURES

- Glass passivated junction chip
- Ideal for printed circuit board
- Reliable low cost construction utilizing molded plastic technique
- Surge overload rating: 175 A peak
- High temperature soldering guaranteed:  
250°C/10sec/ 0.375" (9.5mm) lead length  
at 5 lbs tension

### MECHANICAL DATA

- Terminal: Plated leads solderable per  
MIL-STD 202E, method 208C
- Case: UL-94 Class V-O recognized flame  
retardant epoxy
- Polarity: Polarity symbol marked on body
- Mounting position: Any



### MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS

(Single-phase, half-wave, 60Hz, resistive or inductive load rating at 25°C, unless otherwise stated, for capacitive load, derate current by 20%)

RATINGS	SYMBOL	D8SB 10	D8SB 20	D8SB 40	D8SB 60	D8SB 80	D8SB 100	UNITS
Maximum Repetitive Peak Reverse Voltage	$V_{RRM}$	100	200	400	600	800	1000	V
Maximum RMS Voltage	$V_{RMS}$	70	140	280	420	560	700	V
Maximum DC Blocking Voltage	$V_{DC}$	100	200	400	600	800	1000	V
Maximum Average Forward Rectified Current ( $T_a=70^\circ\text{C}$ )	$I_{F(AV)}$	8.0						A
Peak Forward Surge Current (8.3ms single half sine-wave superimposed on rated load)	$I_{FSM}$	175						A
Maximum Instantaneous Forward Voltage (at forward current 4.0A DC)	$V_F$	1.1						V
Maximum DC Reverse Current (at rated DC blocking voltage) $T_a=25^\circ\text{C}$ $T_a=125^\circ\text{C}$	$I_R$	5 500						$\mu\text{A}$ $\mu\text{A}$
Storage and Operating Junction Temperature	$T_{STG}, T_J$	-55 to + 150						$^\circ\text{C}$